# Octal 3-State Inverting Buffer/Line Driver/Line Receiver

# **High-Performance Silicon-Gate CMOS**

The MC74HC240A is identical in pinout to the LS240. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This octal noninverting buffer/line driver/line receiver is designed to be used with 3-state memory address drivers, clock drivers, and other sub-oriented systems. The device has inverting outputs and two active-low output enables.

The HC240A is similar in function to the HC244A.

#### **Features**

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 120 FETs or 30 Equivalent Gates
- Pb-Free Packages are Available\*



# ON Semiconductor®

http://onsemi.com

# MARKING DIAGRAMS

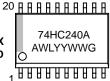


PDIP-20 N SUFFIX CASE 738

20 AAAAAAAAAAA MC74HC240AN O AWLYYWWG

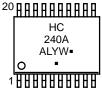


SOIC-20 DW SUFFIX CASE 751D





TSSOP-20 DT SUFFIX CASE 948E





SOEIAJ-20 F SUFFIX CASE 967

A = Assembly Location

WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G = Pb-Free Package
= Pb-Free Package

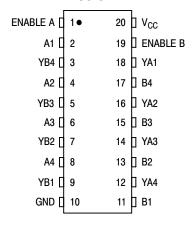
(Note: Microdot may be in either location)

## **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# **PIN ASSIGNMENT**

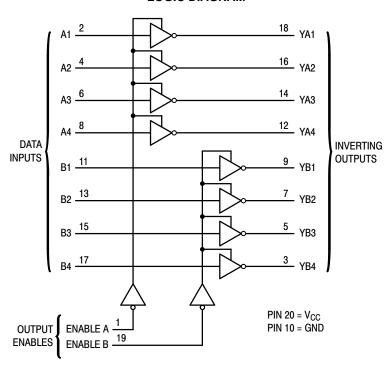


# **FUNCTION TABLE**

| Inpu                  | Outputs |        |
|-----------------------|---------|--------|
| Enable A,<br>Enable B | A, B    | YA, YB |
| L                     | L       | Н      |
| L                     | Н       | L      |
| Н                     | Х       | Z      |

Z = high impedance

# **LOGIC DIAGRAM**



## **ORDERING INFORMATION**

| Device          | Package                   | Shipping <sup>†</sup> |
|-----------------|---------------------------|-----------------------|
| MC74HC240AN     | PDIP-20                   | 18 Units / Box        |
| MC74HC240ANG    | SOIC-20<br>(Pb-Free)      | 18 Units / Box        |
| MC74HC240ADW    | SOIC-20 WIDE              | 38 Units / Rail       |
| MC74HC240ADWG   | SOIC-20 WIDE<br>(Pb-Free) | 38 Units / Rail       |
| MC74HC240ADWR2  | SOIC-20 WIDE              | 1000 Tape & Reel      |
| MC74HC240ADWR2G | SOIC-20 WIDE<br>(Pb-Free) | 1000 Tape & Reel      |
| MC74HC240ADTR2  | TSSOP-20*                 | 2500 Tape & Reel      |
| MC74HC240ADTR2G | TSSOP-20*                 | 2500 Tape & Reel      |
| MC74HC240AF     | SOEIAJ-20                 | 40 Units / Rail       |
| MC74HC240AFG    | SOEIAJ-20<br>(Pb-Free)    | 40 Units / Rail       |
| MC74HC240AFEL   | SOEIAJ-20                 | 2000 Tape & Reel      |
| MC74HC240AFELG  | SOEIAJ-20<br>(Pb-Free)    | 2000 Tape & Reel      |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>This package is inherently Pb-Free.

### **MAXIMUM RATINGS**

|                  | _   |                          |      |
|------------------|---|--------------------------|------|
| Symbol           | Parameter   | Value                    | Unit |
| V <sub>CC</sub>  | DC Supply Voltage (Referenced to GND)   | - 0.5 to + 7.0           | V    |
| V <sub>in</sub>  | DC Input Voltage (Referenced to GND)  | $-0.5$ to $V_{CC} + 0.5$ | V    |
| V <sub>out</sub> | DC Output Voltage (Referenced to GND)   | $-0.5$ to $V_{CC} + 0.5$ | V    |
| I <sub>in</sub>  | DC Input Current, per Pin   | ± 20                     | mA   |
| l <sub>out</sub> | DC Output Current, per Pin  | ± 35                     | mA   |
| I <sub>CC</sub>  | DC Supply Current, V <sub>CC</sub> and GND Pins   | ± 75                     | mA   |
| P <sub>D</sub>   | Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†               | 750<br>500<br>450        | mW   |
| T <sub>stg</sub> | Storage Temperature   | - 65 to + 150            | °C   |
| TL               | Lead Temperature, 1 mm from Case for 10 Seconds<br>(Plastic DIP, SOIC or TSSOP Package) | 260                      | °C   |

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C

SOIC Package: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

# **RECOMMENDED OPERATING CONDITIONS**

| Symbol                             | Parameter  | Min  | Max             | Unit               |    |
|------------------------------------|--|------|-----------------|--------------------|----|
| V <sub>CC</sub>                    | DC Supply Voltage (Referenced to GND)                                      | 2.0  | 6.0             | V                  |    |
| V <sub>in</sub> , V <sub>out</sub> | DC Input Voltage, Output Voltage (Referenced to GN                         | 0    | V <sub>CC</sub> | V                  |    |
| T <sub>A</sub>                     | Operating Temperature, All Package Types                                   | - 55 | + 125           | °C                 |    |
| t <sub>r</sub> , t <sub>f</sub>    | Input Rise and Fall Time $V_{CC} = 2$ (Figure 1) $V_{CC} = 4$ $V_{CC} = 6$ | .5 V | 0<br>0<br>0     | 1000<br>500<br>400 | ns |

# DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

|                 |                                      |   |                          | Gu                        | aranteed Li               | mit                       |      |
|-----------------|--------------------------------------|---|--------------------------|---------------------------|---------------------------|---------------------------|------|
| Symbol          | Parameter                            | Test Conditions   | V <sub>CC</sub>          | – 55 to<br>25°C           | ≤ 85°C                    | ≤ 125°C                   | Unit |
| V <sub>IH</sub> | Minimum High-Level Input Voltage     | $V_{out} = V_{CC} - 0.1 \text{ V}$<br>$ I_{out}  \le 20  \mu\text{A}$   | 2.0<br>3.0<br>4.5<br>6.0 | 1.5<br>2.1<br>3.15<br>4.2 | 1.5<br>2.1<br>3.15<br>4.2 | 1.5<br>2.1<br>3.15<br>4.2 | V    |
| V <sub>IL</sub> | Maximum Low–Level Input Voltage      | $V_{\text{out}} = 0.1 \text{ V}$ $ I_{\text{out}}  \le 20  \mu\text{A}$   | 2.0<br>3.0<br>4.5<br>6.0 | 0.5<br>0.9<br>1.35<br>1.8 | 0.5<br>0.9<br>1.35<br>1.8 | 0.5<br>0.9<br>1.35<br>1.8 | >    |
| V <sub>OH</sub> | Minimum High-Level Output<br>Voltage | $V_{in} = V_{IH}$ $ I_{out}  \le 20 \mu A$  | 2.0<br>4.5<br>6.0        | 1.9<br>4.4<br>5.9         | 1.9<br>4.4<br>5.9         | 1.9<br>4.4<br>5.9         | V    |
|                 |                                      | $ \begin{aligned} V_{in} = V_{IH} &  I_{out}  \leq 2.4 \text{ mA} \\  I_{out}  \leq 6.0 \text{ mA} \\  I_{out}  \leq 7.8 \text{ mA} \end{aligned} $ | 3.0<br>4.5<br>6.0        | 2.48<br>3.98<br>5.48      | 2.34<br>3.84<br>5.34      | 2.2<br>3.7<br>5.2         |      |
| V <sub>OL</sub> | Maximum Low–Level Output<br>Voltage  | $V_{in} = V_{IL}$ $ I_{out}  \le 20 \mu A$  | 2.0<br>4.5<br>6.0        | 0.1<br>0.1<br>0.1         | 0.1<br>0.1<br>0.1         | 0.1<br>0.1<br>0.1         | V    |
|                 |                                      | $\begin{aligned} V_{in} = V_{IL} &  I_{out}  \leq 2.4 \text{ mA} \\  I_{out}  \leq 6.0 \text{ mA} \\  I_{out}  \leq 7.8 \text{ mA} \end{aligned}$   | 3.0<br>4.5<br>6.0        | 0.26<br>0.26<br>0.26      | 0.33<br>0.33<br>0.33      | 0.4<br>0.4<br>0.4         |      |

# DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

|                 |   |  | Gua                  |                 | aranteed Li |         |      |
|-----------------|---|--|----------------------|-----------------|-------------|---------|------|
| Symbol          | Parameter   | Test Conditions  | v <sub>cc</sub><br>v | – 55 to<br>25°C | ≤ 85°C      | ≤ 125°C | Unit |
| l <sub>in</sub> | Maximum Input Leakage Current                     | V <sub>in</sub> = V <sub>CC</sub> or GND   | 6.0                  | ± 0.1           | ± 1.0       | ± 1.0   | μΑ   |
| I <sub>OZ</sub> | Maximum Three–State Leakage<br>Current            | Output in High-Impedance State $V_{in} = V_{IL}$ or $V_{IH}$ $V_{out} = V_{CC}$ or GND | 6.0                  | ± 0.5           | ± 5.0       | ± 10    | μΑ   |
| I <sub>CC</sub> | Maximum Quiescent Supply<br>Current (per Package) | $V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$   | 6.0                  | 4.0             | 40          | 160     | μΑ   |

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

# AC ELECTRICAL CHARACTERISTICS ( $C_L$ = 50 pF, Input $t_r$ = $t_f$ = 6 ns)

|  |  |                          | Gu                    | aranteed Li           | mit                   |      |
|--|--|--------------------------|-----------------------|-----------------------|-----------------------|------|
| Symbol                                 | Parameter  | V <sub>CC</sub><br>V     | – 55 to<br>25°C       | ≤ 85°C                | ≤ 125°C               | Unit |
| t <sub>PLH</sub> ,<br>t <sub>PHL</sub> | Maximum Propagation Delay, A to YA or B to YB (Figures 1 and 3)            | 2.0<br>3.0<br>4.5<br>6.0 | 80<br>40<br>16<br>14  | 100<br>50<br>20<br>17 | 120<br>60<br>24<br>20 | ns   |
| t <sub>PLZ</sub> ,<br>t <sub>PHZ</sub> | Maximum Propagation Delay, Output Enable to YA or YB (Figures 2 and 4)     | 2.0<br>3.0<br>4.5<br>6.0 | 110<br>60<br>22<br>19 | 140<br>70<br>28<br>24 | 165<br>80<br>33<br>28 | ns   |
| t <sub>PZL</sub> ,<br>t <sub>PZH</sub> | Maximum Propagation Delay, Output Enable to YA or YB (Figures 2 and 4)     | 2.0<br>3.0<br>4.5<br>6.0 | 110<br>60<br>22<br>19 | 140<br>70<br>28<br>24 | 165<br>80<br>33<br>28 | ns   |
| t <sub>TLH</sub> ,<br>t <sub>THL</sub> | Maximum Output Transition Time, Any Output (Figures 1 and 3)               | 2.0<br>3.0<br>4.5<br>6.0 | 60<br>23<br>12<br>10  | 75<br>27<br>15<br>13  | 90<br>32<br>18<br>15  | ns   |
| C <sub>in</sub>                        | Maximum Input Capacitance  | -                        | 10                    | 10                    | 10                    | pF   |
| C <sub>out</sub>                       | Maximum Three–State Output Capacitance<br>(Output in High–Impedance State) | -                        | 15                    | 15                    | 15                    | pF   |

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

|          |  | Typical @ 25°C, V <sub>CC</sub> = 5.0 V |    |
|----------|--|---|----|
| $C_{PD}$ | Power Dissipation Capacitance (Per Transceiver Channel)* | 32                                      | pF |

<sup>\*</sup> Used to determine the no–load dynamic power consumption: P<sub>D</sub> = C<sub>PD</sub> V<sub>CC</sub><sup>2</sup>f + I<sub>CC</sub> V<sub>CC</sub>. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

# **SWITCHING WAVEFORMS**

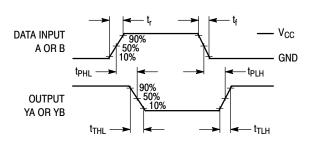


Figure 1.

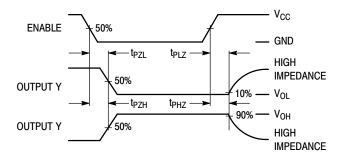
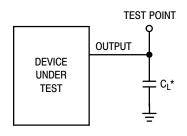
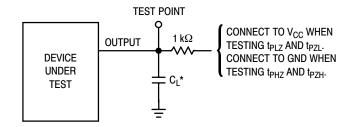


Figure 2.



\*Includes all probe and jig capacitance

Figure 3. Test Circuit



\*Includes all probe and jig capacitance

Figure 4. Test Circuit

# **PIN DESCRIPTIONS**

# **INPUTS**

A1, A2, A3, A4, B1, B2, B3, B4 (Pins 2, 4, 6, 8, 11, 13, 15, 17)

Data input pins. Data on these pins appear in inverted form on the corresponding Y outputs, when the outputs are enabled.

## **CONTROLS**

# Enable A, Enable B (Pins 1, 19)

Output enables (active-low). When a low level is applied to these pins, the outputs are enabled and the devices

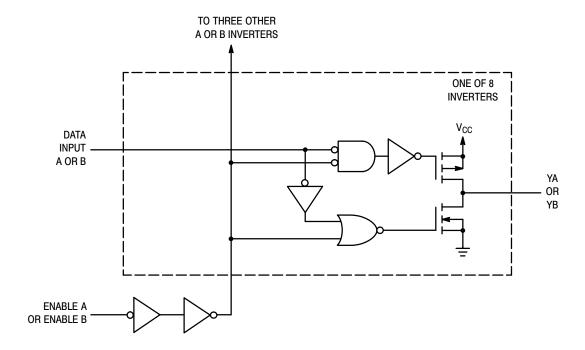
function as inverters. When a high level is applied, the outputs assume the high-impedance state.

# **OUTPUTS**

YA1, YA2, YA3, YA4, YB1, YB2, YB3, YB4 (Pins 18, 16, 14, 12, 9, 7, 5, 3)

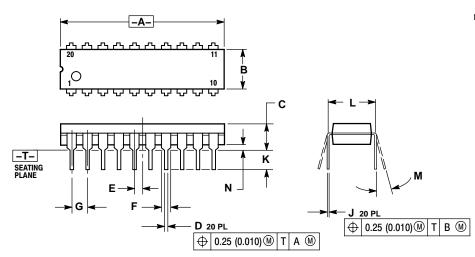
Device outputs. Depending upon the state of the output-enable pins, these outputs are either inverting outputs or high-impedance outputs.

# **LOGIC DETAIL**



# **PACKAGE DIMENSIONS**

# PDIP-20 **N SUFFIX** PLASTIC DIP PACKAGE CASE 738-03 ISSUE E



- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

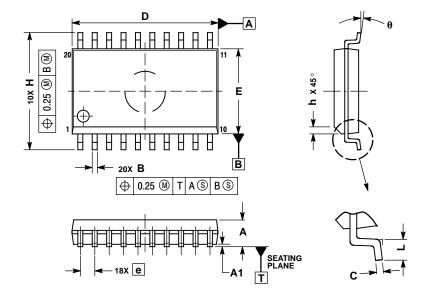
  2. CONTROLLING DIMENSION: INCH.

  3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.

- DIMENSION B DOES NOT INCLUDE MOLD FLASH.

|     | INC   | HES   | MILLIN   | IETERS |
|-----|-------|-------|----------|--------|
| DIM | MIN   | MAX   | MIN      | MAX    |
| Α   | 1.010 | 1.070 | 25.66    | 27.17  |
| В   | 0.240 | 0.260 | 6.10     | 6.60   |
| С   | 0.150 | 0.180 | 3.81     | 4.57   |
| D   | 0.015 | 0.022 | 0.39     | 0.55   |
| Е   | 0.050 | BSC   | 1.27 BSC |        |
| F   | 0.050 | 0.070 | 1.27     | 1.77   |
| G   | 0.100 | BSC   | 2.54     | BSC    |
| J   | 0.008 | 0.015 | 0.21     | 0.38   |
| K   | 0.110 | 0.140 | 2.80     | 3.55   |
| L   | 0.300 | BSC   | 7.62     | BSC    |
| M   | 0 °   | 15°   | 0°       | 15°    |
| N   | 0.020 | 0.040 | 0.51     | 1.01   |

# SOIC-20 **DW SUFFIX** CASE 751D-05 **ISSUE G**

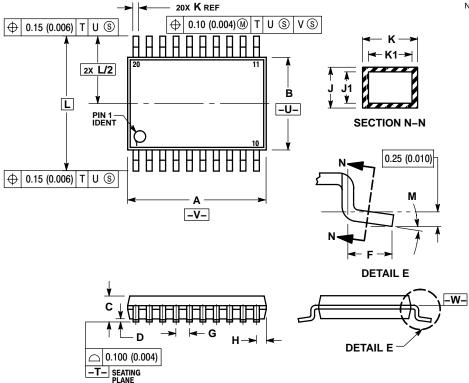


- NOTES:
  1. DIMENSIONS ARE IN MILLIMETERS.
  2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
  3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
  4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
  5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

|     | MILLIN | IETERS |
|-----|--------|--------|
| DIM | MIN    | MAX    |
| Α   | 2.35   | 2.65   |
| A1  | 0.10   | 0.25   |
| В   | 0.35   | 0.49   |
| С   | 0.23   | 0.32   |
| D   | 12.65  | 12.95  |
| Е   | 7.40   | 7.60   |
| е   | 1.27   | BSC    |
| Н   | 10.05  | 10.55  |
| h   | 0.25   | 0.75   |
| L   | 0.50   | 0.90   |
| θ   | 0 °    | 7 °    |

## **PACKAGE DIMENSIONS**

# TSSOP-20 **DT SUFFIX** CASE 948E-02 **ISSUE B**



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION:

  - MILLIMETER.

    3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  - SIDE.

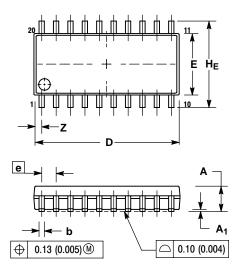
    4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER CIDE.
  - SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

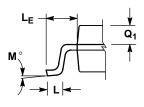
    5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
  - 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
  - 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

|     | MILLIN   | IETERS | INC       | HES   |  |
|-----|----------|--------|-----------|-------|--|
| DIM | MIN      | MAX    | MIN       | MAX   |  |
| Α   | 6.40     | 6.60   | 0.252     | 0.260 |  |
| В   | 4.30     | 4.50   | 0.169     | 0.177 |  |
| С   |          | 1.20   |           | 0.047 |  |
| D   | 0.05     | 0.15   | 0.002     | 0.006 |  |
| F   | 0.50     | 0.75   | 0.020     | 0.030 |  |
| G   | 0.65 BSC |        | 0.026     | BSC   |  |
| Н   | 0.27     | 0.37   | 0.011     | 0.015 |  |
| J   | 0.09     | 0.20   | 0.004     | 0.008 |  |
| J1  | 0.09     | 0.16   | 0.004     | 0.006 |  |
| K   | 0.19     | 0.30   | 0.007     | 0.012 |  |
| K1  | 0.19     | 0.25   | 0.007     | 0.010 |  |
| L   | 6.40     | BSC    | 0.252 BSC |       |  |
| M   | 0°       | 8°     | 0°        | 8°    |  |

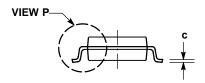
# **PACKAGE DIMENSIONS**

# SOEIAJ-20 **F SUFFIX** CASE 967-01 **ISSUE O**





**DETAIL P** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI

- ILES:
  DIMENSIONING AND TOLERANCING PER ANSI
  Y14.5M, 1982.
  OINTROLLING DIMENSION: MILLIMETER.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD
  FLASH OR PROTRUSIONS AND ARE MEASURED
  AT THE PARTING LINE. MOLD FLASH OR
  PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006)
  PER SIDE.
  TERMINAL NUMBERS ARE SHOWN FOR
  REFERENCE ONLY.
  THE LEAD WIDTH DIMENSION (b) DOES NOT
  INCLUDE DAMBAR PROTRUSION. ALLOWABLE
  DAMBAR PROTRUSION SHALL BE 0.08 (0.003)
  TOTAL IN EXCESS OF THE LEAD WIDTH
  DIMENSION AT MAXIMUM MATERIAL CONDITION.
  DAMBAR CANNOT BE LOCATED ON THE LOWER
  RADIUS OR THE FOOT. MINIMUM SPACE
  BETWEEN PROTRUSIONS AND ADJACENT LEAD
  TO BE 0.46 (0.018). TO BE 0.46 ( 0.018).

|                | MILLIMETERS |       | S INCHES |       |
|----------------|-------------|-------|----------|-------|
| DIM            | MIN         | MAX   | MIN      | MAX   |
| Α              |             | 2.05  |          | 0.081 |
| A <sub>1</sub> | 0.05        | 0.20  | 0.002    | 0.008 |
| b              | 0.35        | 0.50  | 0.014    | 0.020 |
| С              | 0.18        | 0.27  | 0.007    | 0.011 |
| D              | 12.35       | 12.80 | 0.486    | 0.504 |
| Е              | 5.10        | 5.45  | 0.201    | 0.215 |
| е              | 1.27        | BSC   | 0.050    | BSC   |
| HE             | 7.40        | 8.20  | 0.291    | 0.323 |
| L              | 0.50        | 0.85  | 0.020    | 0.033 |
| LE             | 1.10        | 1.50  | 0.043    | 0.059 |
| M              | 0 °         | 10°   | 0 °      | 10 °  |
| $Q_1$          | 0.70        | 0.90  | 0.028    | 0.035 |
| Z              |             | 0.81  |          | 0.032 |

ON Semiconductor and was registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights or the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

# **PUBLICATION ORDERING INFORMATION**

### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 61312, Phoenix, Arizona 85082–1312 USA Phone: 480–829–7710 or 800–344–3860 Toll Free USA/Canada Fax: 480–829–7709 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800–282–9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center 2–9–1 Kamimeguro, Meguro–ku, Tokyo, Japan 153–0051 Phone: 81–3–5773–3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.